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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO. CONFIRMATION 1		
10/634,249	08/04/2003	Dae-Young Kim	51876P356 7777		
8791	7590 06/25/2004		EXAMINER		
	SOKOLOFF TAYLOR &	PHAM, HOAI V			
	HIRE BOULEVARD, SEVI LES,  CA   90025	ART UNIT	PAPER NUMBER		
EOD / IT (ODE	20, 011 70025		2814		
			DATE MAILED: 06/25/2004		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Appli	cation No.	Applicant(s)			
		10/63	4,249	KIM, DAE-YOUNG			
	Office Action Summary	Exam	iner	Art Unit			
			V Pham	2814			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply							
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.  - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.  - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).  Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).							
Status							
1)⊠	Responsive to communication(s) fil	ed on 04 August 2	<u>2003</u> .				
2a)□	This action is FINAL.						
3)□	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.						
Disposit	ion of Claims						
5)□ 6)⊠ 7)□	4)						
Applicat	ion Papers						
9)⊠ The specification is objected to by the Examiner.							
10) ☐ The drawing(s) filed on is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.							
	Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.							
Priority	under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  a) All b) Some * c) None of:  1. Certified copies of the priority documents have been received.  2. Certified copies of the priority documents have been received in Application No  3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).  * See the attached detailed Office action for a list of the certified copies not received.							
2) Noti 3) Info	nt(s) ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review rmation Disclosure Statement(s) (PTO-1449 er No(s)/Mail Date <u>04 August 2003</u> .		4) Interview Summa Paper No(s)/Mail 5) Notice of Informa 6) Other:				

#### **DETAILED ACTION**

### Specification

1. The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

## Claim Rejections - 35 USC § 112

2. Claims 1-6 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

Claim 1, the phrase "forming a source and a drain doped with a first conductivity type in an active area on both sides of each word line by an isolation layer of a second conductivity type doped substrate" renders the claim indefinite. It is not clear how "a source and a drain doped with a first conductivity type in an active area on both sides of each word line" can be formed by "an isolation layer of a second conductivity type doped substrate". It is not clear where to form each word line. It is not clear how an isolation layer can have a second conductivity type. Is "an isolation layer" in line 5 the same with "isolation layers" in line 9? Is the "source" doped with both a first conductivity type (lines 3-4) and a second conductivity type (lines12-13)?

The phrase "an interval which is wider in the source than in the drain" renders the claim indefinite. The scope of the claim can not be defined. It is not clear what "an interval which is wider in the source than in the drain" means.

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Claim 3, line 2, "a twist" should be changed to --the tilt angle--.

Claim 4, the phrase "the tilt ion implantation process carried out in a direction perpendicular to the word line" renders the claim indefinite. It is not clear how the tilt ion implantation can be perpendicular to the word line.

Claim 6, line 1, delete "of fabricating the semiconductor device".

# Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

4. Claims 1-6, insofar as clear, are rejected under 35 U.S.C. 102(b) as being anticipated by Krivokapic et al. [U.S. Pat. 6,008,094].

Krivokapic et al. (figs. 4-5, cols. 4-5) discloses a method of fabricating a semiconductor device, comprising the step of:

forming a gate electrode (16) on a substrate;

forming an isolation layer (19) on the gate electrode and the substrate, wherein the isolation layer having an expose portion on a source region;

implanting boron into the source region by using the isolation layer (19) as an ion implanting mask during a tilt ion implantation process, wherein the tilt ion implantation process is carried out using a tilt angle of about 7° to 25°.

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#### Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hoai V Pham whose telephone number is 571-272-1715. The examiner can normally be reached on 9:30A.M. - 8:00P.M..

- 6. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M. Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.
- 7. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hoai Pham June 11, 2004